

REMARKS/ARGUMENTS

Claims 29-38 stand rejected under 35 U.S.C. 102(b) as being anticipated by Kawasaki; claims 29-38 stand rejected under 35 U.S.C. 102(e) as being anticipated by Huster.

The examiner is aware that a patent is its own lexicographer. The examiner is directed to Figure 1 of the instant invention that illustrates implanted region 12b implanted beneath the channel region 24. Figures 7-10 that illustrates region 212 implanted beneath the channel region. The Webster's II New Riverside Dictionary gives the meaning of the word beneath to be (1) In or to a lower position, or (2) underneath. Taken in context of the written disclosure and the Figures described above, the meaning of the word beneath as it is used in the instant patent application can only be underneath. The examiners attempt to redefine the meaning of the word beneath as it is used in the claim is clearly incorrect. The carbon doped regions described in the Kawasaki patent are not beneath the channel as the word beneath is used in the instant claims and claims 29-38 are allowable over the Kawasaki patent.

The Huster patent describes implanting carbon 44 into a semiconductor substrate 42. The Huster patent then describes forming a silicon layer 46 over the carbon implanted region 44. The examiner states that a compressive stress is induced into channel region and cites the following sections of the Huster patent (Figures 2A-2D and col. 3-line 66 to col. 5-line 20). The Huster patent does not however describe the formation of a compressive stress in the channel region. If the examiner insists that the Huster patent describes the formation of a compressive stress, then the examiner is requested to point out with particularity the regions in the Huster patent that disclose or teach the formation this compressive stress. In fact, the Huster patent does not teach the formation of a compressive stress in the channel region. The Huster patent teaches the formation of a step retrograde doping profile. The word stress is not used anywhere in the Huster patent. Claims 29, 32, and 35 all comprise the limitation of implanting a species in a semiconductor beneath a MOS gate structure so as to induce stress in a

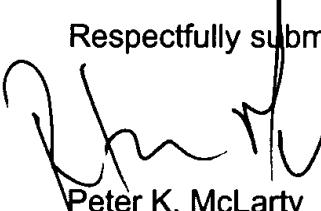
region. This limitation is clearly not found in the Huster patent and claims 29, 32 and 35 are allowable over the Huster patent. In addition claims 30, 31, 33, 34 and 36-38 all depend on either claim 29, 32 or 35 and contain the limitations of these claims. Claims 30, 31, 33, 34 and 36-38 are therefore also allowable over the cited art.

In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant response places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



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